

# ION IMPLANTATION METHODS AND TRANSISTOR CELL LAYOUT FOR FIN TYPE TRANSISTORS

## Abstract of Disclosure

Fin-type field effect transistors are fabricated on a semiconductor substrate . Rectangular fins are formed on the substrate in a rectangular pattern of rows and columns and gate electrodes are deposited on at least two sides of the fins. The gate electrodes are implanted with ions at an angle  $\theta$  to a line perpendicular to the substrate, such that  $D \approx H \tan \theta$  , where D is the distance between fins in adjacent rows or columns and H is the height of the fins.

## Figures